Lecture22: NMOS inverter (2)

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After all,

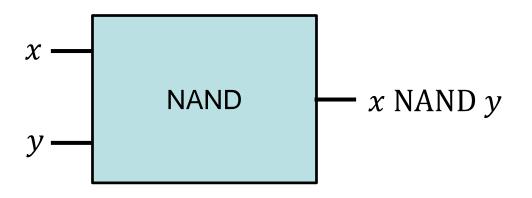
- As much as we have AND, OR, and NOT gates, we can implement any Boolean function.
 - For example, x XOR y = (x AND (NOT y)) OR ((NOT x) AND y)
 - With <u>NAND</u>, <u>NOR</u>, <u>and NOT gates</u>, we can, too.

Inverter and NAND

NOR can be implemented similarly.



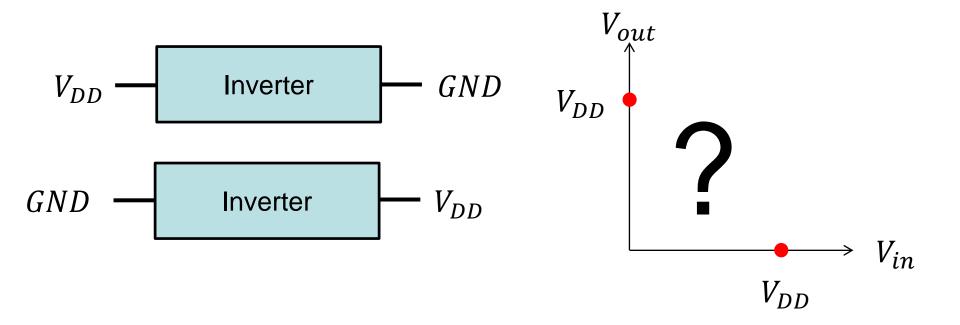
| x | NOT |
|---|-----|
| 0 | 1 |
| 1 | 0 |



| x | y | NAND |
|---|---|------|
| 0 | 0 | 1 |
| 0 | 1 | 1 |
| 1 | 0 | 1 |
| 1 | 1 | 0 |

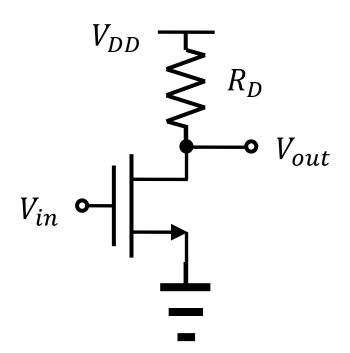
In circuit,

- How can we represent 0 and 1?
 - V_{DD} is assigned to the logical value, 1.
 - GND is assigned to the logical value, 0.



NMOS inverter

- How can we have an output, 0?
 - Only when the input is high. <u>You have seen it before!</u>



| Vin | Vout |
|-----|------|
| 0 | 1 |
| 1 | 0 |

Voltage transfer

- When $V_{in} < V_{TH}$, trivially, $V_{out} = V_{DD}$.
- When V_{in} is slightly larger than V_{TH} , the NMOSFET is in the saturation region.

$$V_{out} = V_{DD} - I_D R_D$$

$$V_{out} = V_{DD} - \frac{1}{2} \mu_n C_{ox} \frac{W}{L} R_D (V_{in} - V_{TH})^2$$

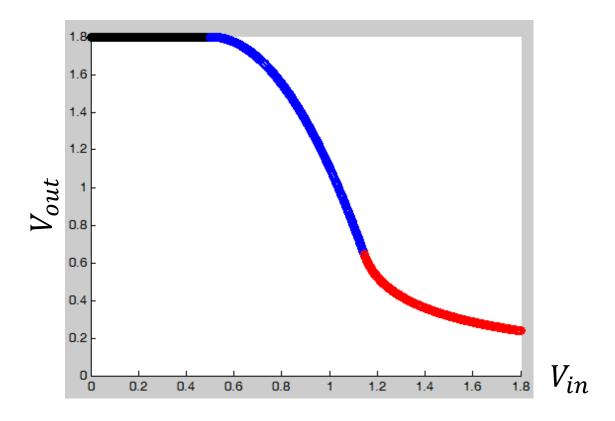
• When V_{in} is further increased, the NMOSFET is in the triode region.

$$V_{out} = V_{DD} - \frac{1}{2} \mu_n C_{ox} \frac{W}{L} R_D [2(V_{in} - V_{TH})V_{out} - V_{out}^2]$$

Draw it! (1/2)

Parameters in Example 17. 14 (Razavi) w/o modification.

$$\mu_n C_{ox} = 100 \ \mu\text{A/V}^2$$
, $V_{TH} = 0.5 \ \text{V}$, $\frac{W}{L} = \frac{10}{0.18}$, $R_D = 1k\Omega$ and $V_{DD} = 1.8 \ \text{V}$

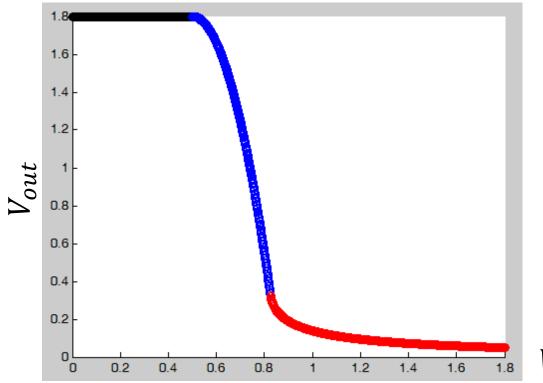


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Draw it! (2/2)

With a wider NMOSFET

$$\mu_n C_{ox} = 100 \ \mu\text{A/V}^2$$
, $V_{TH} = 0.5 \ \text{V}$, $\frac{W}{L} = \frac{50}{0.18}$, $R_D = 1k\Omega$ and $V_{DD} = 1.8 \ \text{V}$



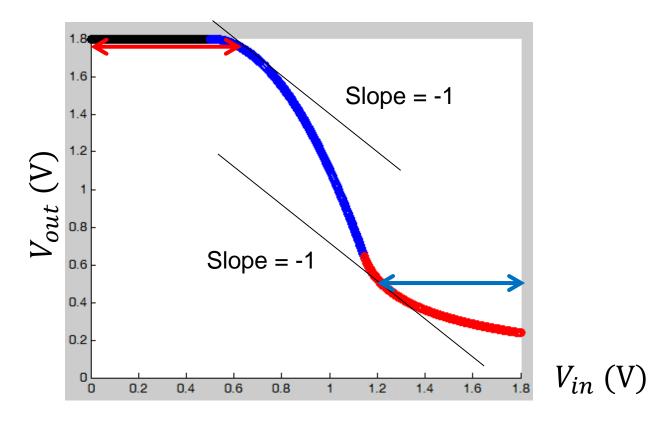
 V_{in}

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Noise margin

Verbatim

- "(It) is the maximum amount of degradation (noise) at the input that can be tolerated before the output is affected significantly."



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Noise margin of CS stage

- Let's calculate $NM_L = V_{IL}$.
 - In this case, (blue curve)

$$V_{out} = V_{DD} - \frac{1}{2} \mu_n C_{ox} \frac{W}{L} R_D (V_{in} - V_{TH})^2$$

- Taking the differentiation w. r. t. V_{in} ,

$$\frac{\partial V_{out}}{\partial V_{in}} = -\mu_n C_{ox} \frac{W}{L} R_D (V_{in} - V_{TH})$$

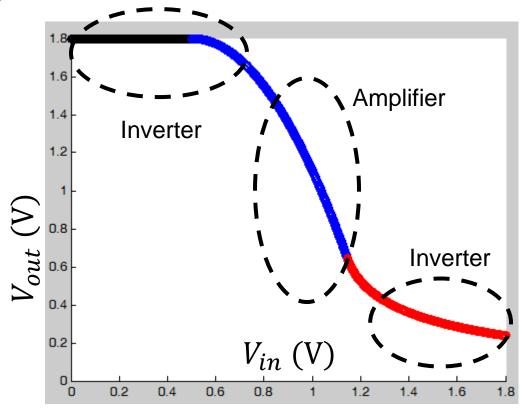
- At $V_{in} = V_{IL}$, the slope becomes -1,

$$NM_L = V_{IL} = \frac{1}{\mu_n C_{ox} \frac{W}{L} R_D} + V_{TH}$$

- (Stronger NMOS yields a reduces NM_L .)

Common-source

- Common-source configuration
 - It can be used as an inverter.
 - It can be used as an amplifier.
 - $\frac{dV_{out}}{dV_{in}}$ is the voltage gain.



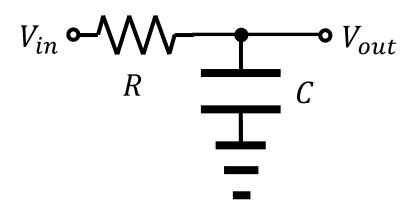
RC circuit

- Consider a serial RC circuit.
 - The KCL states

$$\frac{V_{out} - V_{in}}{R} + C \frac{dV_{out}}{dt} = 0$$

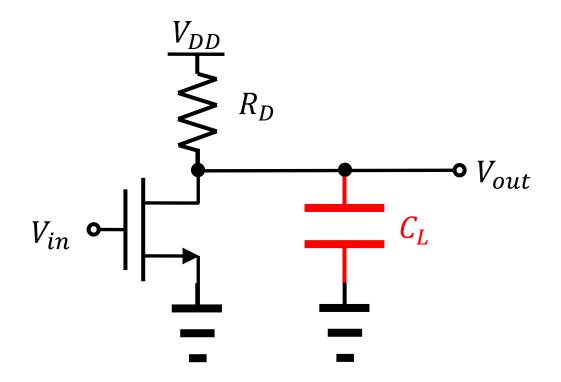
- Assume a step-wise change of V_{in} at t=0. It becomes V_{DD} .
- Initial output voltage is V_0 .
- Its solution is given by

$$V_{out}(t) = V_{DD} + (V_0 - V_{DD}) \exp\left(-\frac{t}{RC}\right)$$



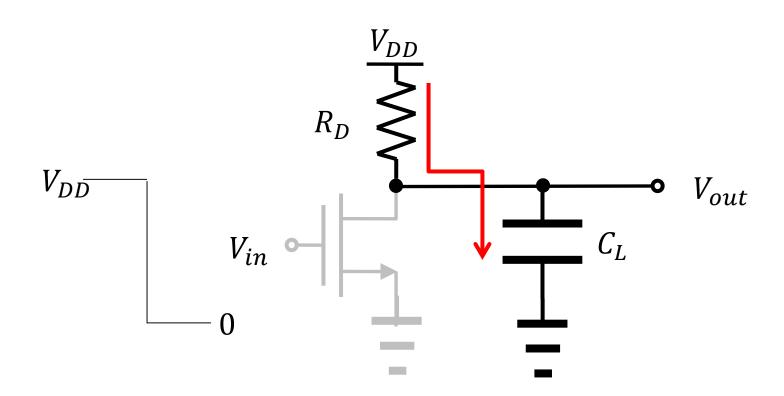
Speed of inverter (1/4)

- VTC merely describes the DC behavior.
 - Input voltages with different frequencies (1 kHz, 1 MHz, 1 GHz, ...)
 - Time-dependent behavior



Speed of inverter (2/4)

- A rapid transition of V_{in} from V_{DD} to 0
 - The capacitor should be charged.



Speed of inverter (3/4)

- Simply, it is a RC circuit.
 - Then, the solution is simply

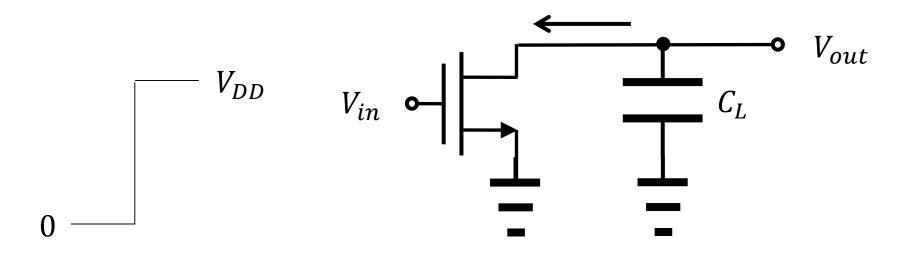
$$V_{out}(t) = V_{out}(0^{-}) + [V_{DD} - V_{out}(0^{-})] \left(1 - \exp\frac{-t}{R_D C_L}\right)$$

- Since $\exp(-3) \approx 0.05$, after $3R_DC_L$, V_{out} reaches 0.95 V_{DD} .
- Yes, it takes time to get the stable output voltage...
- The delay restricts the maximum signal frequency.

Speed of inverter (4/4)

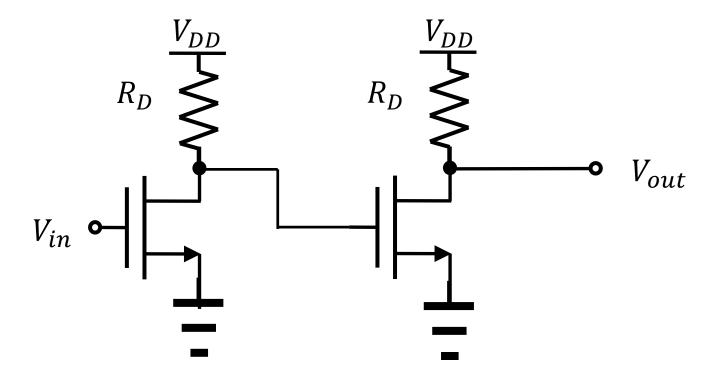
- A rapid transition of V_{in} from 0 to V_{DD} to 0
 - At the initial phase, the resistor does not conduct.
 - Also the MOSFET is operated in its saturation mode. Then,

$$I_{D,sat} + C_L \frac{dV_{out}}{dt} = 0$$



Origin of C_L ?

- Consider an inverter chain.
 - Then, what is the load capacitance for the first stage?



Interconnect